

Synthesis and Characterization of the First Liquid Single-Source Precursors for the Deposition of Ternary Chalcopyrite (CuInS₂) Thin Film Materials

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The fabrication of polycrystalline chalcopyrite absorber layers for thin film solar cells has received considerable interest due to the potential of these materials as the next generation of photovoltaic devices.¹ Chalcopyrite materials are highly appealing given their band gaps are near optimum for either implementation in space (AM0) or terrestrial applications (AM1.5). For example, a Cu(In,Ga)Se₂-based thin film solar cell has been reported to display an AM1.5 conversion of 18.8%.² A further challenge for space applications is the optimization of mass specific power to minimize power system launch costs. This requirement necessitates the use of lightweight substrates such as metal foils, or polymer substrates, which require the use of reduced-temperature processes, typically <400 °C. Consequently, greater demand has been placed on the synthesis of new precursors capable of producing chalcopyrite materials at reduced temperatures. Clearly, molecular engineering of MOCVD precursors plays a significant role and is receiving greater attention.³ Ternary single-source precursors (type I–III–IV₂) provide an attractive and clean approach; however, very few are known or have been tested.

In the course of our investigations for improved precursors for the chemical vapor deposition (CVD) of chalcopyrite thin films,^{4–6} we have discovered new liquid single-source precursors to the ternary semicon-

ductor CuInS₂, based on the [P(R)₃]₂Cu(SR')₂In(SR')₂ architecture.⁷ Manipulation of the steric and electronic properties of the neutral donor ligand and the thiol moiety permits directed adjustment of the physical and thermal properties of the precursor. Use of extended alkyl groups resident either on the phosphine or on thiol groups affords the liquid derivatives [P(*n*-Bu)₃]₂Cu-(SEt)₂In(SEt)₂ (**1**) and [P(*n*-Bu)₃]₂Cu(S(*n*-Pr))₂In(S(*n*-Pr))₂ (**2**), respectively.

The complexes are synthesized based on a modification of the procedure reported by Kanatzidis,⁷ with the thiol derivative being generated in situ by reaction of the conjugate acid with NaOEt in methanol, thus producing no adverse side products, in addition to an "activated" thiolate. The multistage synthesis yields the desired products in good yields (>65%), as opaque liquids that are stable in air for over 5 h, during normal handling.⁸ One of the key features of these new precursors is their liquid phase, which is remarkable considering their high molecular mass and stoichiometry, thus facilitating the possibility of a solvent-free delivery and higher deposition rates during thin film fabrication. Needless to say, the precursors also display very high solubility in both polar and nonpolar organic solvents, which may be attributed to their ionic character and to the nonpolar alkyl groups resident on the phosphine.

Multinuclear NMR, low-temperature differential scanning calorimetry (DSC), and thermogravimetric analyses (TGA) with evolved gas analysis (EGA) were used to characterize and verify precursor formation and purity. NMR data demonstrated that **1** and **2** were free from any starting reagents (see Supporting Information). ³¹P NMR spectra show a shift for PBu₃, from -32.50 to -19.2 for [P(Bu)₃]₂Cu{MeCN}₂⁺PF₆⁻, -22.4 for **1** and -22.5 ppm for **2**, which is indicative of ligand to metal coordination and hence complex formation.⁹ Low-temperature DSC provided information on the thermal stability and temperature-dependent phase changes of the single source precursors. The samples were heated at a rate of 10 °C/min under a dinitrogen

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(8) For **1**: ¹H NMR: 300 MHz; CDCl₃; δ 2.75 ppm (q, CH₃CH₂S-); δ 1.57 ppm (br m, P(CH₂C₃H₇)₃); δ 1.42 ppm (br m, P(CH₂C₂H₄CH₃)₃); δ 1.32 ppm (t, -SCH₂CH₃); δ 0.94 ppm (t, P(CH₂C₂H₄CH₃)₃). ¹³C NMR: 75 MHz; CDCl₃; δ 26.66 ppm (P(CH₂C₃H₇)₃); δ 24.88 ppm (P(CH₂CH₂-C₂H₅)₃); δ 24.83 ppm (P(C₂H₄CH₂CH₃)₃); δ 23.22 ppm (-SCH₂CH₃); δ 20.87 ppm (-SCH₂CH₃); δ 13.89 ppm (P(C₂H₄CH₂CH₃)₃). ³¹P NMR: 121 MHz; CDCl₃; δ -21.42 ppm (br s, -Cu{P(Bu)₃}₂). Complex **2** was prepared in a manner similar to **1**: ¹H NMR: 300 MHz; CDCl₃; δ 2.69 ppm (t, C₂H₅CH₂S-); δ 1.56 ppm (br m, P(CH₂C₃H₇)₃ overlapping with CH₃CH₂CH₂S-); δ 1.41 ppm (br m, P(CH₂C₂H₄CH₃)₃); δ 0.94 ppm (m, CH₃CH₂CH₂S- overlapping with P(C₃H₆CH₃)₃). ¹³C NMR: 75 MHz; CDCl₃; δ 30.92 ppm (CH₃CH₂CH₂S-); δ 28.73 ppm (CH₃CH₂-CH₂S-); δ 26.66 ppm (P(CH₂C₃H₇)₃); δ 24.96 ppm (P(CH₂CH₂C₂H₅)₃); δ 24.85 ppm (P(C₂H₄CH₂CH₃)₃); δ 13.91 ppm (P(C₂H₄CH₂CH₃)₃); δ 13.71 ppm (CH₃CH₂CH₂S-). ³¹P NMR: 121 MHz; CDCl₃; δ -21.38 ppm (br s, -Cu{P(Bu)₃}₂).

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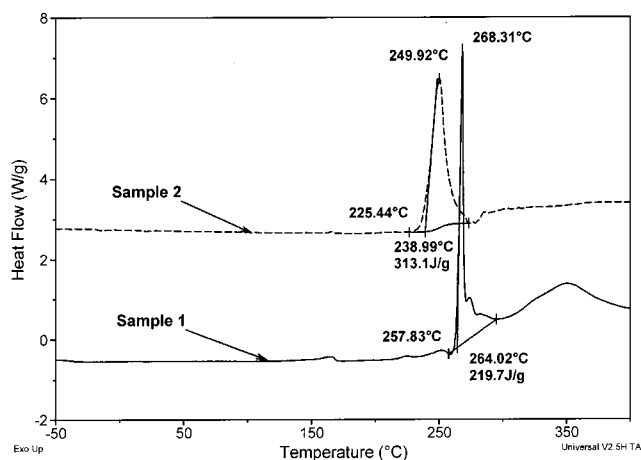


Figure 1. Low-temperature DSC Studies.

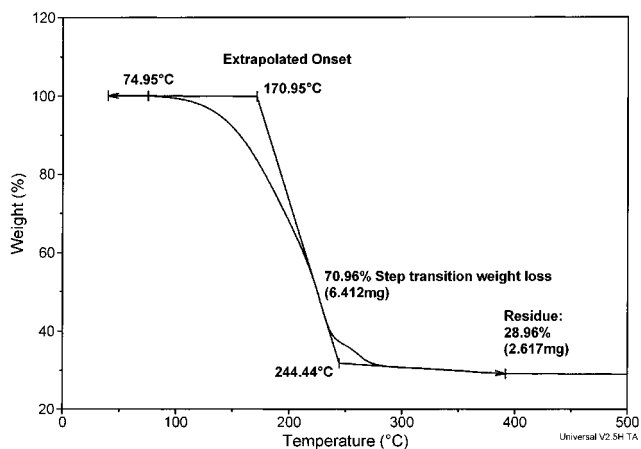


Figure 2. TGA profile for $[\{P(n\text{-Bu})_3\}_2\text{Cu}(S(n\text{-Pr}))_2\text{In}(S(n\text{-Pr}))_2]$, **2**.

atmosphere, using hermetically sealed aluminum pans to eliminate weight loss associated with vaporization. The low-temperature DSC profiles show an absence of an endotherm assignable to a melting phase transition, thus confirming their liquid phases at ambient temperatures (Figure 1). The main exothermic events for **1** and **2** begin with onset temperatures of 258 and 225 °C with large exotherms of 220 and 313 J/g, respectively, which can be assigned to the decomposition of the samples. The lower decomposition temperature of **2** is as expected since an increase in chain length and/or steric "bulk" of the alkyl groups is reported to decrease stability.^{3c,10}

Thermogravimetric analyses (TGA) were performed at ambient pressure in platinum pans on samples of the liquid precursors. The samples were heated at a rate of 20 °C/min under a dinitrogen atmosphere to correlate with EGA. Weight loss was associated with decomposition of the complexes (Figure 2). Calculation of the derivative maximum rate of weight loss (MRW, %/°C), and step transition weight loss were used as a measure of relative stability. The TGA curves show a smooth loss of mass over a temperature window of approximately

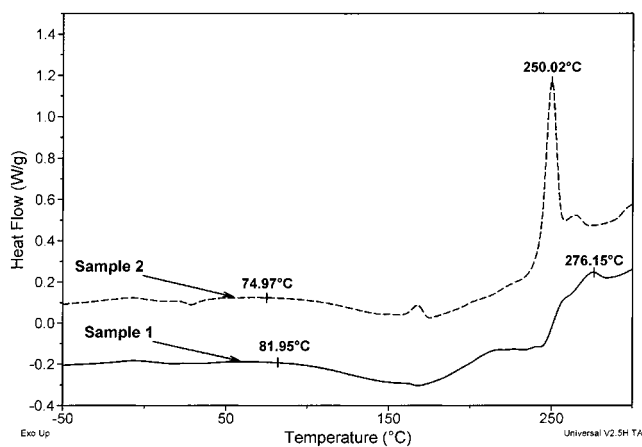


Figure 3. Low-temperature MDSC for $[\{P(n\text{-Bu})_3\}_2\text{Cu}(\text{SET})_2\text{-In}(\text{SET})_2]$ (**1**) and $[\{P(n\text{-Bu})_3\}_2\text{Cu}(S(n\text{-Pr}))_2\text{In}(S(n\text{-Pr}))_2]$ (**2**).

170 °C, accounting for a loss of 70% for **1** and 71% for **2**, of the original material where the MRW is found at 238 and 225 °C, respectively. The TGA profile for samples **1** and **2** indicate an initial weight loss, as low as 82 and 75 °C, while calculation of the extrapolated onset temperatures yields 189 and 171 °C, respectively. Calculation of the precursor efficiency for **1** and **2** to afford CuInS_2 as the final product shows both samples to be within 1.5% based on the residual material from the TGA experiments. Preliminary vacuum-TGA studies on **1** shows the degradation temperature window to be as low as 100–160 °C, thus making these precursors ideal candidates for use in low-temperature CVD on space-qualified substrates such as Kapton.

Interestingly, TGA data indicates that both precursors begin to decompose at much lower temperatures than that observed by DSC analysis. To resolve this issue, low-temperature modulated differential scanning calorimetry (MDSC) was undertaken, which provides information about the reversible (heat capacity) and nonreversible (kinetic) characteristics of thermal events, thereby providing greater sensitivity to deconvolute thermal phase transitions.¹¹ MDSC profiles for samples **1** and **2** show an onset for an endothermic phase transition occurring at ≈ 80 and 75 °C, respectively, which correlate with the decomposition temperatures found in TGA, while the exothermic maxima (T_{max}) are of a magnitude constant with those found in the DSC experiments (Figure 3). Hence, MDSC supports the TGA decomposition data. A more thorough interpretation of the thermal properties of these materials is presented elsewhere.⁶

The mode of decomposition for the liquid precursors **1** and **2** was investigated by FTIR and mass spectroscopic EGA. The FTIR spectra for **1** (Figure 4) show absorptions at ≈ 3000 , 1460, 1390, 1300, and 1250 cm^{-1} , which are assignable to the initial expulsion of diethyl sulfide. Correlation with the mass spectra supports these findings on the basis of the library fit and from the assignment of the fragment and parent ions ($m/z = 90$). After ≈ 15 min the intensity of the absorptions in the IR spectra due to diethyl sulfide decrease; however, absorptions in the aliphatic regions are still evident. Comparison with the respective mass spectra allows for

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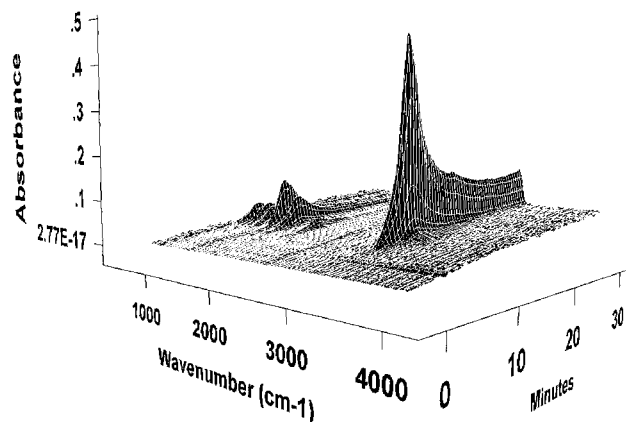


Figure 4. EGA-FTIR spectra for $[\{P(n\text{-Bu})_3\}_2\text{Cu}(\text{SEt})_2\text{In}(\text{SEt})_2]$ (**1**).

the assignment to the loss of PBU_3 , with a library fit of 92% and assignment of the parent ion ($m/z = 202$). Importantly, mass spectroscopic EGA shows the absence of any fragment ions with an isotopic pattern associated with an indium derivative. In a similar experiment, EGA for the *n*-propyl derivative gave analogous results.

The ability of the new precursor to thermally decompose to yield single-phase CuInS_2 was investigated by powder X-ray diffraction (XRD) analysis and energy-dispersive spectroscopy (EDS) on the nonvolatile solids from the TGA experiments and vacuum pyrolysis (5 mm Hg, 150–300 °C). XRD spectra for the nonvolatile material produced from the pyrolysis of **1** confirmed it to be single-phase CuInS_2 (Figure 5). Examination of the EDS spectra for the same samples shows predominant emissions due to Cu, In, and S edges, with the approximate percentage atomic composition of 27, 23, and 50 for **1** and 28, 23, and 49 for **2**, respectively, thus supporting the stoichiometric formation of CuInS_2 , albeit slightly copper-rich.¹² The stoichiometry of CIS deposition is known to be temperature-dependent,^{4b} and so these initial results are very promising.

(12) Samples were characterized by transmission spectroscopy (Perkin-Elmer, Lambda-19), scanning electron microscopy (SEM) (Hitachi S-3000N), energy-dispersive spectroscopy (EDS) (EDAX, accurate to $\pm 3\%$), XRD (Philips PW3710, Cu $K\alpha$, 1.541), and thermal analysis (TA Instruments Models: Hi-Res-TGA-2950, DSC-910, and MDSC-2920).

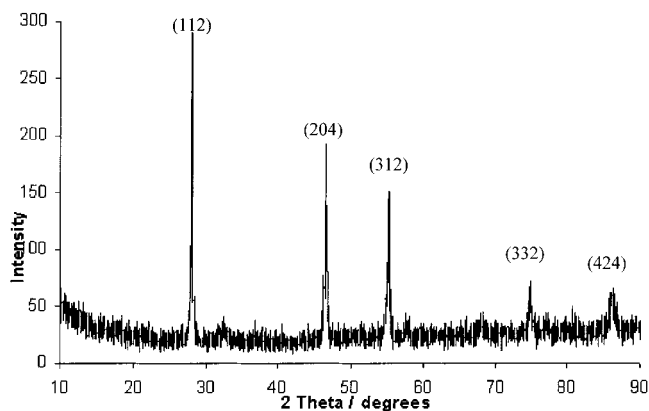


Figure 5. XRD powder diffraction for nonvolatile residue from pyrolysis of $[\{P(n\text{-Bu})_3\}_2\text{Cu}(\text{SEt})_2\text{In}(\text{SEt})_2]$ (Cu $K\alpha$, 1.541 Å).

In summary, we have produced the first known liquid single-source precursors for the deposition of the ternary chalcopyrite CuInS_2 . Thermal analysis supports that selective adjustment of the sterically demanding groups either on the donor group or chalcogenide permits adjustment of the solid-state phase and stability of the precursor. Furthermore, the availability of a liquid-phase precursor dramatically broadens the potential for a number of MOCVD processes and may allow application to certain spin-coating processes, fabrication of CuInS_2 quantum dots, and impregnated CIS₂ polymer films.

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Supporting Information Available: Synthetic scheme for **1** and **2**. ¹H, ¹³C, and ³¹P NMR spectra of **1**, **2**, and starting reagents. TGA data for **1**. Vacuum TGA data for **1**. X-ray powder diffraction data for **1** and **2**. EDS data and spectra for **1** and **2**. SEM pictures of CuInS_2 from **1** and **2**. FTIR spectra (EGA) for **2**. Mass spectra (EGA) for **1** and **2** (PDF). This material is available free of charge via the Internet at <http://pubs.acs.org>.

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